Vishay Siliconix



www.vishay.com

N-Channel 80 V (D-S) MOSFET



PRODUCT SUMMARY								
V _{DS} (V)	80							
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 10 \text{ V}$	0.038							
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 7.5 \text{ V}$	0.046							
Q _g typ. (nC)	7.1							
I _D (A) ^a	12							
Configuration	Single							

FEATURES

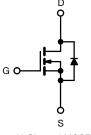
- TrenchFET® Gen IV power MOSFET
- Tuned for the lowest R_{DS} x Q_{oss}
- 100% R_q and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS COMPLIANT HALOGEN FREE

APPLICATIONS

- · Primary side switch
- DC/DC converter
- Motor drive switch
- Boost converter
- LED backlighting



N-Channel MOSFET

ORDERING INFORMATION						
Package	PowerPAK SC-70					
Lead (Pb)-free and halogen-free	SiA108DJ-T1-GE3					

ABSOLUTE MAXIMUM RATING	iS (T _A = 25 °C, ι	ınless otherv	vise noted)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage	V _{DS}	80	V	
Gate-source voltage	Gate-source voltage			V
	T _C = 25 °C		12 ^a	
0 1: 1 : 1 (T 150 00)	T _C = 70 °C	1 . [12 ^a	
Continuous drain current (T _J = 150 °C)	T _A =25 °C	l _D	6.6 ^{b, c}	
	T _A = 70 °C	1 [5.3 b, c	A
Pulsed drain current (t = 100 μs)	I _{DM}	30	^	
	T _C = 25 °C	,	12 ^a	
Continuous source-drain diode current	T _A = 70 °C	l _S	2.9 b, c	
Single pulse avalanche current	L = 0.1 mH	I _{AS}	12	
Single pulse avalanche energy	L=0.1 mn	E _{AS}	7.2	mJ
	T _C = 25 °C		19	
Maximum power dissipation	T _C = 70 °C	T _ [12	W
	T _A = 25 °C	P _D	3.5 b, c	VV
	T _A = 70 °C	Ī [2.2 b, c	
Operating junction and storage temperature	T _J , T _{stg}	-55 to +150	°C	
Soldering recommendations (peak tempera		260		

THERMAL RESISTANCE RATINGS									
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT				
Maximum junction-to-ambient b, f	t ≤ 5 s	R _{thJA}	28	36	°C/W				
Maximum junction-to-case (drain)	Steady state	R_{thJC}	5.3	6.5	7 °C/W				

Notes

- a. Package limited
- b. Surface mounted on 1" x 1" FR4 board
- t = 5 s
- See solder profile (www.vishav.com/doc?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- f. Maximum under steady state conditions is 80 °C/W



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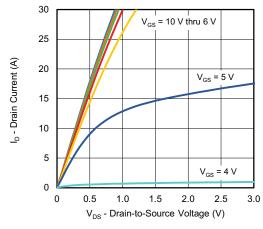
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static					•	•
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	80	-	-	V
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$	I _D = 250 μA	-	60	-	
V _{GS(th)} temperature coefficient	ΔV _{GS(th)} /T _J	I _D = 250 μA	-	-6.8	-	mV/°C
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2	-	4	V
Gate-source leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	100	nA
Zava mata valtama duain avuunnt		V _{DS} = 80 V, V _{GS} = 0 V	-	-	1	
Zero gate voltage drain current	I _{DSS}	V _{DS} = 80 V, V _{GS} = 0 V, T _J = 70 °C	-	-	10	μA
On-state drain current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	10	-	-	Α
Drain aguras en etata registance 3	В	V _{GS} = 10 V, I _D = 4 A	-	0.032	0.038	
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 7.5 V, I _D = 2 A	-	0.034	0.046	Ω
Forward transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 15 A	-	28	-	S
Dynamic ^b						
Input capacitance	C _{iss}		-	545	-	pF
Output capacitance	C _{oss}	$V_{DS} = 40 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	75	-	
Reverse transfer capacitance	C _{rss}		-	9	-	
Tatalandania	0	V _{DS} = 40 V, V _{GS} = 10 V, I _D = 4 A	-	9.2	13	nC
Total gate charge	Qg		-	7.1	10	
Gate-source charge	Q _{gs}	$V_{DS} = 40 \text{ V}, V_{GS} = 7.5 \text{ V}, I_D = 4 \text{ A}$	-	2.8	-	
Gate-drain charge	Q _{gd}		-	1.7	-	
Output charge	Q _{oss}	V _{DS} = 40 V, V _{GS} = 0 V	-	9	-	
Gate resistance	R _q	f = 1 MHz	0.3	1.3	2.6	Ω
Turn-on delay time	t _{d(on)}		-	10	20	
Rise time	t _r	$V_{DD} = 40 \text{ V}, R_L = 10 \Omega, I_D \cong 4 \text{ A},$	-	5	10	1
Turn-off delay time	t _{d(off)}	$V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	14	30	Ī
Fall time	t _f		-	5	10	ns
Turn-on delay time	t _{d(on)}		-	11	20	
Rise time	t _r	$V_{DD} = 40 \text{ V}, R_L = 10 \Omega, I_D \cong 4 \text{ A},$	-	5	10	
Turn-off delay time	t _{d(off)}	$V_{GEN} = 7.5 \text{ V}, R_g = 1 \Omega$	-	12	25	
Fall time	t _f		-	5	10	
Drain-Source Body Diode Characteristi	cs				•	
Continuous source-drain diode current	I _S	T _C = 25 °C	-	-	12	
Pulse diode forward current	I _{SM}		-	-	30	A
Body diode voltage	V _{SD}	I _S = 4 A, V _{GS} = 0 V	-	0.82	1.2	V
Body diode reverse recovery time	t _{rr}	- 	-	30	60	ns
Body diode reverse recovery charge	Q _{rr}	$I_F = 4 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s},$	-	25	50	nC
Reverse recovery fall time	t _a	$T_J = 25 ^{\circ}\text{C}$	-	20	-	
Reverse recovery rise time	t _b		_	10	_	ns

Notes

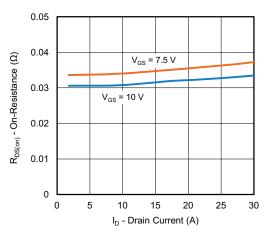
- a. Pulse test: pulse width \leq 300 μ s, duty cycle \leq 2 %
- b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

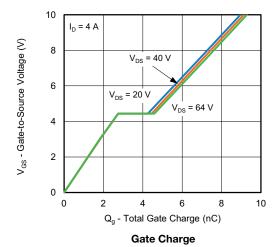


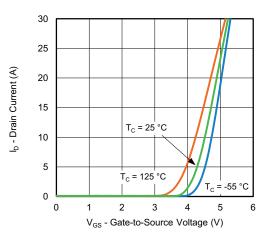


Output Characteristics

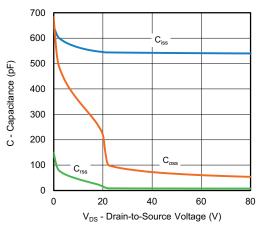


On-Resistance vs. Drain Current and Gate Voltage

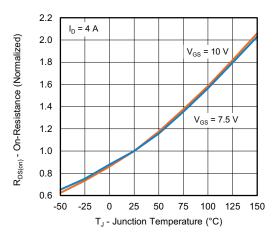




Transfer Characteristics

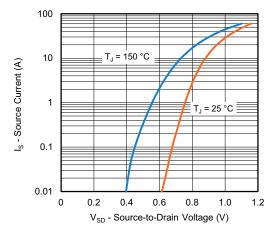


Capacitance

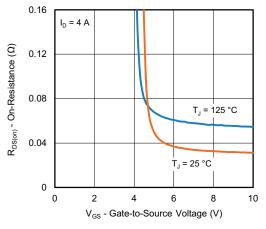


On-Resistance vs. Junction Temperature

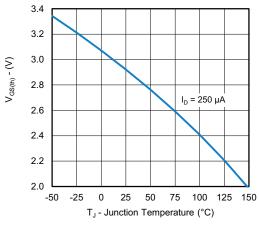




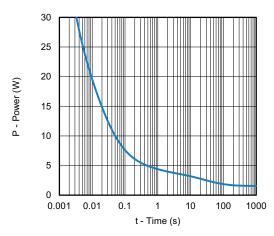
Source-Drain Diode Forward Voltage



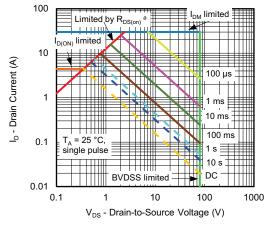
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power, Junction-to-Ambient

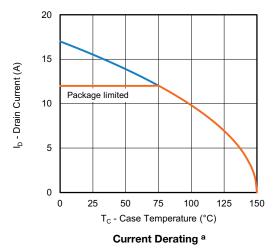


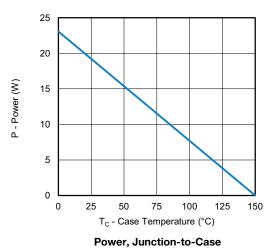
Safe Operating Area, Junction-to-Ambient

Note

a. V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified



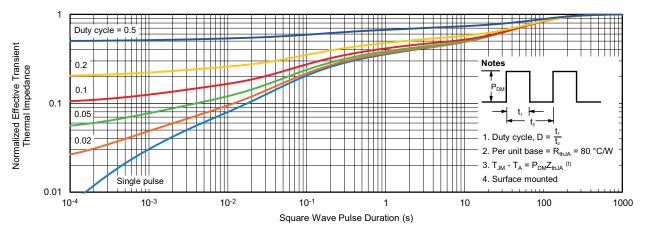




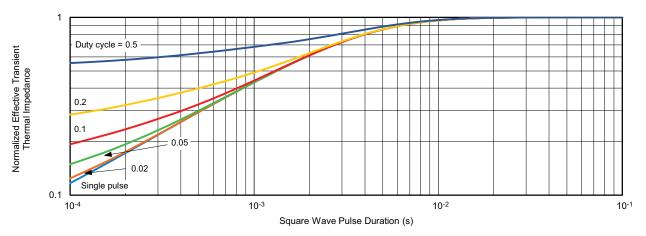
Note

a. The power dissipation P_D is based on T_J max. = 25 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit





Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?77827.





Vishay Siliconix

PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
 Package outline exclusive of mold flash and metal burr
 Package outline inclusive of plating

	SINGLE PAD						DUAL PAD					
DIM	MILLIMETERS			INCHES			MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
D1	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028
D2	0.135	0.235	0.335	0.005	0.009	0.013						
Е	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041
E2	0.345	0.395	0.445	0.014	0.016	0.018						
E3	0.425	0.475	0.525	0.017	0.019	0.021						
е		0.65 BSC			0.026 BSC	;	0.65 BSC			0.026 BSC		
K		0.275 TYP			0.011 TYP	1	0.275 TYP			0.011 TYP		
K1		0.400 TYP			0.016 TYP		0.320 TYP			0.013 TYP		
K2		0.240 TYP		0.009 TYP		0.252 TYP			0.010 TYP			
К3		0.225 TYP		0.009 TYP						•	•	
K4		0.355 TYP		0.014 TYP								
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015
T							0.05	0.10	0.15	0.002	0.004	0.006

ECN: C-07431 - Rev. C, 06-Aug-07

DWG: 5934

06-Aug-07



RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Single



Dimensions in mm/(Inches)

Return to Index

ATTLICATION NOT



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